Current-Shunt Monitor, Voltage Output, Bi-Directional Zero-Drift

The NCS199A1, NCS199A2 and NCS199A3 are voltage output current shunt monitors that can measure voltage across shunts at common–mode voltages from –0.3 V to 26 V, independent of supply voltage. Three fixed gains are available: 50 V/V, 100 V/V or 200 V/V. The low offset of the zero–drift architecture enables current sensing with maximum drops across the shunt as low as 10 mV full–scale.

The devices can operate from a single +2.7 V to +26 V power supply, drawing a maximum of $100~\mu A$ of supply current. All versions are specified over the extended operating temperature range ($-40^{\circ}C$ to $+125^{\circ}C$).

Features

- Wide Common–Mode Input Range –0.3 V to 26 V
- Supply Voltage Range from 2.7 V to 26 V
- Low Offset Voltage ±150 μV Max
- Low Offset Drift (0.5 μV/°C)
- Low Gain Error (max 1.5%)
- Rail-to-rail Input and Output Capability
- Low Current Consumption (typ 65 μA, 100 μA max)
- NCV Prefix for Automotive and Other Applications Requiring Unique Site Qualified and PPAP Capable
- These are Pb-free Devices

Typical Applications

- Current Sensing (High-Side/Low-Side)
- Automotive
- Telecom
- Sensors



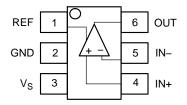
ON Semiconductor®

www.onsemi.com



SC70-6 SQ SUFFIX CASE 419B

PIN CONNECTIONS



MARKING DIAGRAM



XXX = Specific Device Code (See page 4)

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

Product	Gain	R3-R4	R1-R2
NCS199A1	50	20 kΩ	1 ΜΩ
NCS199A2	100	10 kΩ	1 ΜΩ
NCS199A3	200	5 kΩ	1 ΜΩ

$$\mathbf{V}_{\mathsf{OUT}} = \left(\mathbf{I}_{\mathsf{LOAD}} \times \mathbf{R}_{\mathsf{SHUNT}}\right) \! \mathbf{GAIN} + \mathbf{V}_{\mathsf{REF}}$$

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 4 of this data sheet.

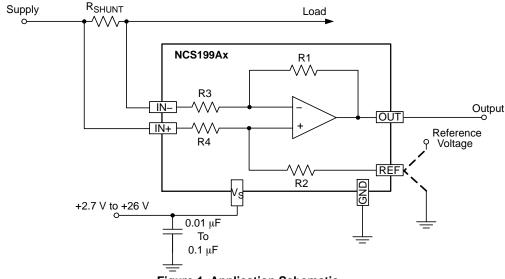


Figure 1. Application Schematic

Table 1. MAXIMUM RATINGS

Rating Supply Voltage (Note 1)			Value	Unit	
			+26	V	
Analog Inputs	Differential (V _{IN+})-(V _{IN-})	$V_{IN+,}V_{IN-}$	-26 to +26	V	
	Common-Mode (Note 2)		GND-0.3 to +26		
REF Input		V_{REF}	GND-0.3 to (V _s) +0.3	V	
Output (Note 2)		V _{OUT}	GND-0.3 to (V _s) +0.3	V	
Input Current into Any Pin (Note 2)			5	mA	
Maximum Junction Temperature		T _{J(max)}	+150	°C	
Storage Temperature Range		TSTG	-65 to +150	°C	
ESD Capability, Human Body Mode	I (Note 3)	HBM	±3000	V	
ESD Capability, Machine Model (No	te 3)	MM	±100	V	
Charged Device Model (Note 3)		CDM	±1000	V	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for safe operating parameters.
- 2. Input voltage at any pin may exceed the voltage shown if current at that pin is limited to 5 mA.
- 3. This device series incorporates ESD protection and is tested by the following methods
 - ESD Human Body Model tested per AEC-Q100-002 (EIA/JESD22-A114)
 - ESD Machine Model tested per AEC-Q100-003 (EIA/JESD22-A115)
 - ESD Charged Device Model tested per AEC-Q100-011.
 - Latchup Current Maximum Rating: 50 mA per JEDEC standard: JESD78

Table 2. THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Characteristics, SC70 (Note 4) Thermal Resistance, Junction-to-Air (Note 5)	$R_{ heta JA}$	250	°C/W

- Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for safe
 operating parameters.
- 5. Values based on copper area of 645 mm² (or 1 in²) of 1 oz copper thickness and FR4 PCB substrate.

Table 3. RECOMMENDED OPERATING RANGES

Rating		Min	Max	Unit
Supply Voltage	V _S	2.7	26	V
Ambient Temperature	T _A	-40	125	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

Table 4. ELECTRICAL CHARACTERISTICS Boldface limits apply over the specified temperature range, $T_A = -40^{\circ}C$ to 125°C, guaranteed by characterization and/or design. At $T_A = +25^{\circ}C$, $V_{SENSE} = V_{IN+} - V_{IN-}$, and $V_{REF} = V_S/2$, unless otherwise noted.

Parameter		Test Conditions	Symbol	Min	Тур	Max	Unit
GAIN							
NCS199A1			G		50		V/V
NCS199A2					100		
NCS199A3			_		200		
Gain Error		$V_{SENSE} = -5 \text{ mV to } 5 \text{ mV}$	G _e		±0.2	±1.5	%
Gain Error vs. Tem	perature	$T_A = -10^{\circ}C \text{ to } 125^{\circ}C$			7	20	ppm/°C
Nonlinearity Error		$V_{SENSE} = -5 \text{ mV to } 5 \text{ mV}$			±0.01		%
Maximum Capaciti		No sustained oscillation			1		nF
VOLTAGE OFFSE	Т		1		1	•	1
Offset Voltage (RT	l Note 6)	V _{SENSE} = 0 mV	Vos		±5.0	±150	μV
Offset Drift No	CS199A2, NCS199A3 NCS199A1		δV/δΤ		0.1 0.5	0.6 2.0	μV/°C
INPUT							
Input Bias Current		V _{SENSE} = 0 mV	I _{IB}			60	μΑ
Common-Mode In	put Voltage Range		V_{CM}	-0.3		26	V
Common–Mode Rejection Ratio	NCS199A2, NCS199A3	$V_S = 5 \text{ V}, V_{IN+} = 2 \text{ V to } +26 \text{ V}, V_{SENSE} = 0 \text{ mV}$	CMRR	100	115		dB
		V _S = 3.3 V, V _{IN+} = 3 V to +26 V, V _{SENSE} = 0 mV		100	115		dB
		$V_S = 3.3 \text{ V}, V_{\text{IN+}} = 0 \text{ V to +26 V}, \\ V_{\text{SENSE}} = 0 \text{ mV } (T_A = -10^{\circ}\text{C to }85^{\circ}\text{C})$		100	120		dB
Common–Mode Rejection Ratio	NCS199A1	$V_S = 5 \text{ V}, V_{IN+} = 2 \text{ V to } +26 \text{ V}, V_{SENSE} = 0 \text{ mV}$	CMRR	97	110		dB
		$V_S = 3.3 \text{ V}, V_{IN+} = 3 \text{ V to } +26 \text{ V}, \\ V_{SENSE} = 0 \text{ mV}$		97	110		dB
		$V_S = 3.3 \text{ V}, V_{IN+} = 0 \text{ V to } +26 \text{ V}, \\ V_{SENSE} = 0 \text{ mV } (T_A = -10^{\circ}\text{C to } 85^{\circ}\text{C})$		97	115		dB
OUTPUT							
Output Voltage Lov	N	Referenced from GND $R_L=10~\text{k}\Omega$ to Ground	V _{OL}		5	50	mV
Output Voltage Hig	h	Referenced from V _S $R_L = 10 \text{ k}\Omega$ to Ground	V _{OH}		0.05	0.2	V
DYNAMIC PERFO	RMANCE						
Bandwidth (f _{-3dB})		C_{LOAD} = 10 pF, NCS199A1 C_{LOAD} = 10 pF, NCS199A2 C_{LOAD} = 10 pF, NCS199A3	BW		100 60 40		kHz
Slew Rate			SR		0.4		V/µs
NOISE			<u> </u>		ı	1	
Spectral Density, 1	kHz (RTI Note 6)		e _n		35		nV/√Hz
POWER SUPPLY	(/		-11			<u> </u>	,,,,,
Operating Voltage	Range	V _{SENSE} = 0 mV	V _s	2.7		26	V
Quiescent Current		V _{SENSE} = 0 mV	I _{DD}		65	100	μΑ
Quiescent Current	over Temperature	V _{SENSE} = 0 mV	-00		"	115	μΑ
Power Supply Rejection Ratio		V _S = +2.7 V to +26 V, V _{IN+} =18 V, V _{SENSE} = 0 mV	PSRR		±0.1	±10	μV/V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. RTI = referenced—to—input.

ORDERING INFORMATION

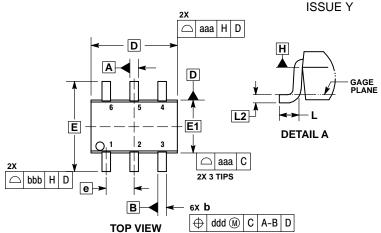
Device	Gain	Marking	Package	Shipping [†]
NCS199A1SQT2G	50	ACQ		
NCS199A2SQT2G	100	ACR	SC70-6 (Pb-Free)	3000 / Tape and Reel
NCS199A3SQT2G	200	ACP	(1.5.1.55)	

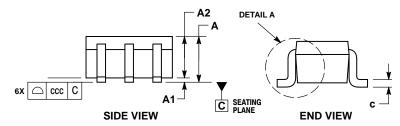
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363

CASE 419B-02



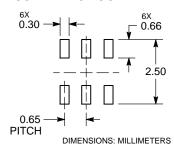


NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
 DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF
- THE PLASTIC BODY AND DATUM H.
 DATUMS A AND B ARE DETERMINED AT DATUM H.
- DIMENSIONS 6 AND 6 APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
- 7. DIMENSION 5 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION 5 AT MAXIMUM MATERIAL CONDI-TION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α			1.10			0.043	
A1	0.00		0.10	0.000		0.004	
A2	0.70	0.90	1.00	0.027	0.035	0.039	
b	0.15	0.20	0.25	0.006	0.008	0.010	
С	0.08	0.15	0.22	0.003	0.006	0.009	
D	1.80	2.00	2.20	0.070	0.078	0.086	
E	2.00	2.10	2.20	0.078	0.082	0.086	
E1	1.15	1.25	1.35	0.045	0.049	0.053	
е	0.65 BSC			0	.026 BS	С	
L	0.26	0.36	0.46	0.010	0.014	0.018	
L2	0.15 BSC			0.006 BSC			
aaa	0.15 0.006						
bbb	0.30			0.012			
ccc	0.10				0.004		
ddd	0.10				0.004		

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and the are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative